

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Canceled)
2. (Currently Amended) A resist underlayer anti-reflective coating forming composition for use in a lithography process of manufacture of a semiconductor device comprising:
  - a polymer compound produced by addition polymerization having an epoxy group;
  - a compound with a molecular weight of 2000 or less having at least two carboxyl groups, or protected carboxyl groups; ~~and~~
  - ~~a solvent;~~ a solvent; and
  - a light absorbing compound.wherein the resist underlayer anti-reflective coating forming composition contains no strong acid catalyst.
3. (Previously Presented) A resist underlayer anti-reflective coating forming composition for use in a lithography process of manufacture of a semiconductor device comprising:
  - an s-triazine trione skeleton compound with a molecular weight of 2000 or less having at least two epoxy groups;
  - a polymer compound having a phenolic hydroxyl group, a carboxyl group, a protected carboxyl group or an acid anhydride structure; and
  - a solvent,wherein the resist underlayer anti-reflective coating forming composition contains no strong acid catalyst.

4. (Currently Amended) A resist underlayer anti-reflective coating forming composition for use in a lithography process of manufacture of a semiconductor device comprising:

a solvent; and

a polymer compound having ~~a carboxyl group or a protected carboxyl group,~~  
group and an epoxy group,

wherein the resist underlayer anti-reflective coating forming composition contains no strong acid catalyst.

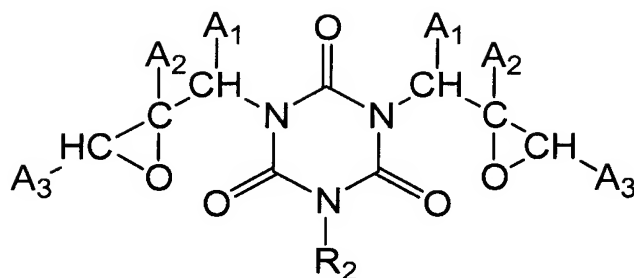
5. (Previously Presented) The underlayer coating forming composition according to claim 3, wherein the polymer compound having a carboxyl group is a compound having acrylic acid or methacrylic acid as a unit structure.

6. (Previously Presented) The underlayer coating forming composition according to claim 3, wherein the polymer compound having a phenolic hydroxyl group is a compound having hydroxystyrene as a unit structure.

7. (Original) The underlayer coating forming composition according to claim 3, wherein the compound with a molecular weight of 2000 or less having at least two epoxy groups is a compound having at least three epoxy groups and no aromatic ring structure.

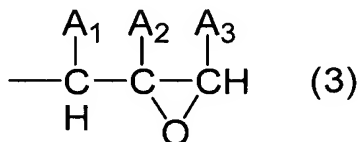
8. (Canceled)

9. (Original) The underlayer coating forming composition according to claim 3, wherein the compound with a molecular weight of 2000 or less having at least two epoxy groups is a compound of formula (2)



(2)

wherein A<sub>1</sub>, A<sub>2</sub> and A<sub>3</sub> each are hydrogen atom, methyl group or ethyl group, R<sub>2</sub> is hydrogen atom, C<sub>1-6</sub> alkyl group, C<sub>3-6</sub> alkenyl group, benzyl group, phenyl group or a group of formula (3)



(3)

10-12. (Canceled)

13. (Currently Amended) A method for forming photoresist ~~pattern-patterns~~ for use in manufacture of semiconductor ~~device~~devices, comprising

coating ~~the an~~ underlayer forming composition ~~according to claim 2~~ on a semiconductor substrate, and baking it to form an underlayer coating,

forming a photoresist layer on the underlayer coating,

exposing the semiconductor substrate covered with the underlayer coating and the photoresist layer to light, and

developing the photoresist layer after the exposure to ~~light-light~~, wherein the underlayer forming composition comprises:

a polymer compound produced by addition polymerization having an epoxy group;

a compound with a molecular weight of 2000 or less having at least two carboxyl groups, or protected carboxyl groups; and

a solvent,

wherein the resist underlayer anti-reflective coating forming composition contains no strong acid catalyst.

14. (Original) The method for forming photoresist pattern according to claim 13, wherein the exposure to light is carried out with a light of a wavelength of 248 nm, 193 nm or 157 nm.